

國立交通大學
電子工程學系電子研究所
碩士論文

超細薄膜奈米雙閘場效電晶體含括返向通量比
之物理解析式模型



**A Physically Based Analytic Model Including Backward to
Forward Flux Ratio for Ultrathin Film Double-Gate MOSFETs**

研究生：林盈秀 Ying-Shiou Lin

指導教授：陳明哲 Prof. Ming-Jer Chen

中華民國 九十四 年 七 月

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